AMENDMENTS TO THE SPECIFICATION:

Please amend the following paragraph beginning at page 1, line 16 and ending at page 1, line 22 as follows:

First, as shown in FIG. **10A**, a substrate **11** held in a horizontal state by a substrate holding mechanism **12** is immersed in a plating solution **10** in circulation. Then, the substrate **11** is rotated together with the substrate holding mechanism **12** at a speed of rotation of 30 rpm by using a control device (not shown). An electrode **13** for contacting the surface of the substrate **11** to be plated and a seal **17** (not shown) for contacting the surface to be plated in such a manner as to protect the electrode **13** from the plating solution **10** have been mounted on the substrate holding mechanism **12**.

Please amend the following paragraph beginning at page 10, line 1 and ending at page 10, line 9 as follows:

First, as shown in FIG. **2A**, a first interlayer insulating film **152** is formed on a substrate **151**, while a lower-layer wire **153** (not shown) composed of a TaN barrier film **153a** and a Cu film **153b** is buried in the first interlayer insulating film **152**. Subsequently, a second interlayer insulating film **154** is formed on each of the lower-layer wire **153** and the first interlayer insulating film **152**. Then, a depressed portion composed of a hole reaching the lower-layer wire **153** and a trench for an upper-layer wire is formed in the second interlayer insulating film **154**. Thereafter, a TaN barrier film **155** and a Cu seed film **156** are deposited successively on the second interlayer insulating film **154** including the depressed portion in such a manner as to fill the depressed portion midway.

plated but in tilted relation therewith. In other words, the contact angle of the seal **210b** relative to the surface of the substrate **209** to be plated is in a range larger than 90° when viewed from the center of the substrate **209**, preferably in a rage not less than 120° and not more than 150°.

Please amend the following paragraph beginning at page 13, line 22 and ending at page 14, line 3 as follows:.

In the case of spraying the pure water **113** (not shown) onto the surface of the Cu seed film **104**, however, relatively large bubbles **114** are formed disadvantageously in the pure water **113** adsorbed to the surface of the Cu seed film **104**. In the present embodiment, therefore, there are cases where the bubbles **114** each having a size exceeding about several micrometers remain on the surface of the Cu seed film **104** at the time at which the substrate **101** is immersed in the plating solution **106**, though the total number of bubbles adsorbed to the surface of the Cu seed film **104** is reduced at that time.

Please amend the following paragraph beginning at page 26, line 22 and ending at page 27, line 11 as follows:

FIG. **8** is an enlarged view of the portion of the substrate holding mechanism **210** supporting the substrate **209**. As shown in FIG. **8**, the substrate holding mechanism **210** is provided with a cathode electrode **210a** for contacting the surface of the substrate **209** to be plated and a seal ~~**210a**~~ **210b** for contacting the surface of the substrate **209** to be plated in such a manner as to protect the cathode electrode **210a** from the plating solution **200**. Thus, as shown in FIG. **7B**, plating growth can be performed by applying a voltage between the anode electrode **205** and the cathode electrode **210a** with the substrate **209** being immersed in the plating solution **200** reserved in the plating bath **204**, i.e., by applying a voltage between the anode electrode **205** and the surface of the substrate **209** to be plated (e.g., the surface of a Cu seed layer). The present embodiment has another characteristic in that the portion of the seal **210b** supporting the substrate **209** is not in vertical positional relation with the surface of the substrate **209** to be